



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

RS2A THRU RS2M 2.0 AMP SURFACE MOUNT FAST RECOVERY RECTIFIERS



FEATURES

- * Ideal for surface mount applications
- * Easy pick and place
- * Built-in strain relief
- * Fast switching speed

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Metallurgically bonded construction
- * Polarity: Color band denotes cathode end
- * Mounting position: Any
- * Weight: 0.093 grams

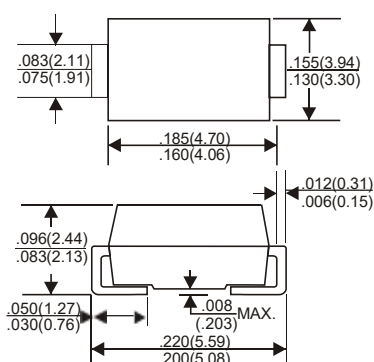
VOLTAGE RANGE

50 to 1000 Volts

CURRENT

2.0 Ampere

DO-214AA(SMB)



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25 °C ambient temperature unless otherwise specified.

Single phase half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

TYPE NUMBER	RS2A	RS2B	RS2D	RS2G	RS2J	RS2K	RS2M	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at Ta=90 C	2.0							A
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	50							A
Maximum Instantaneous Forward Voltage at 2.0A	1.3							V
Maximum DC Reverse Current Ta=25°C	5.0							A
at Rated DC Blocking Voltage Ta=125 C	300							A
Maximum Reverse Recovery Time (Note 1)	150				250	500		nS
Typical Junction Capacitance (Note 2)	50							pF
Operating and Storage Temperature Range T _J , T _{STG}	-65—+150							°C

NOTES:

1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

RATING AND CHARACTERISTIC CURVES (RS2A THRU RS2M)

FIG.1-TYPICAL FORWARD CHARACTERISTICS

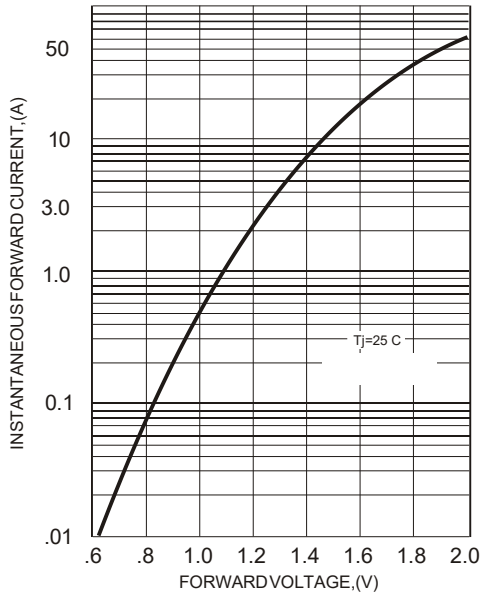


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

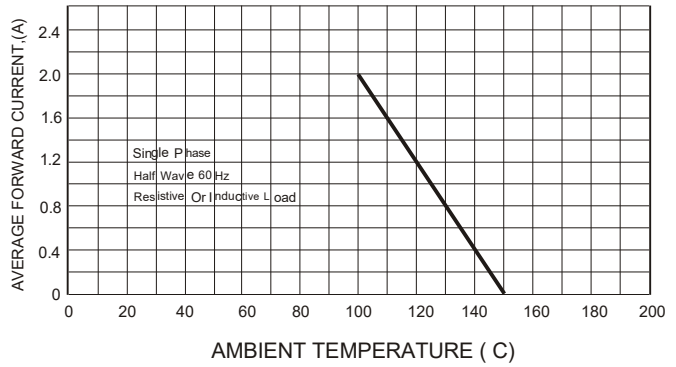


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

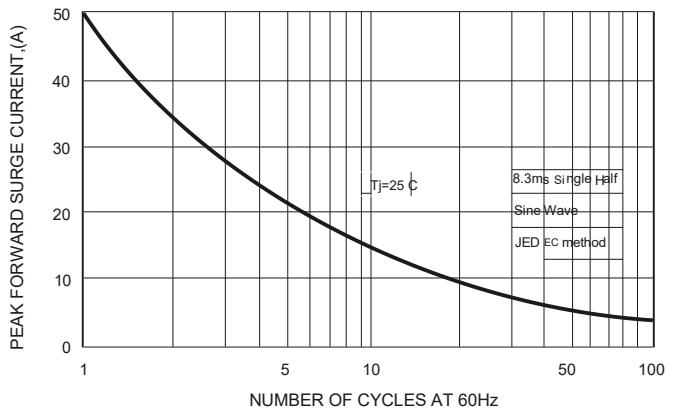
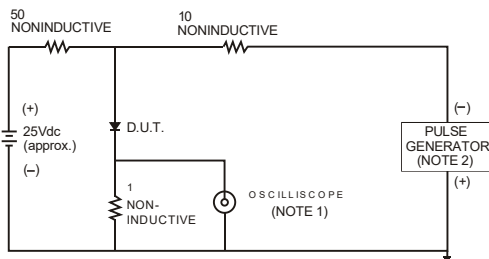


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm, 22pF.
2. Rise Time= 10ns max., Source Impedance= 50 ohms.

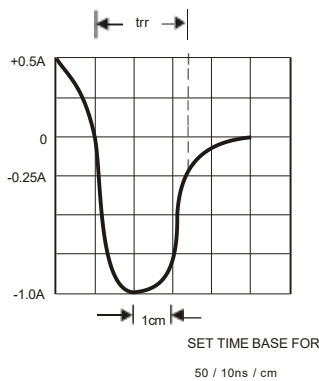


FIG.5-TYPICAL JUNCTION CAPACITANCE

